

isc Silicon NPN Power Transistor

2SC4327

DESCRIPTION

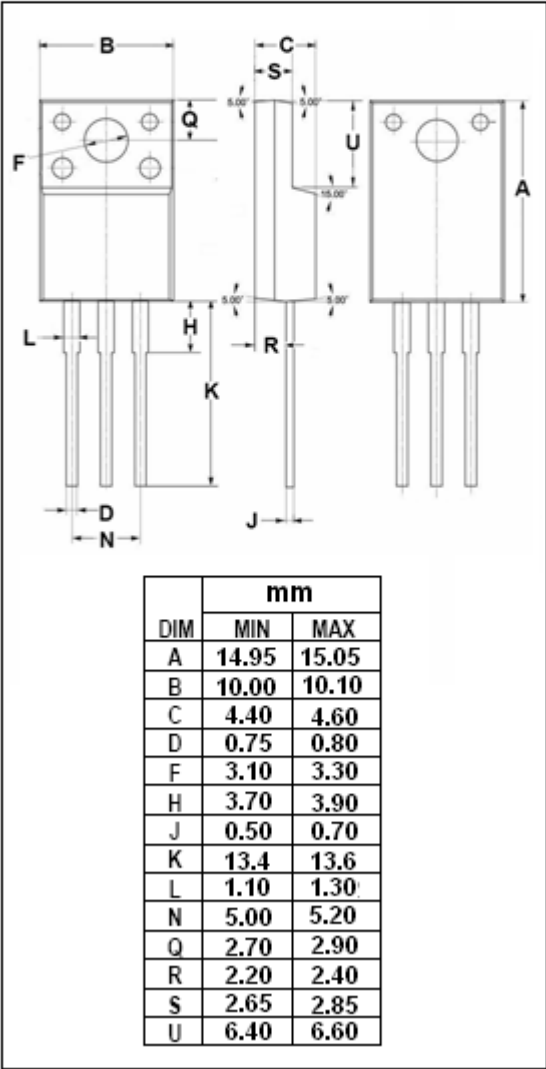
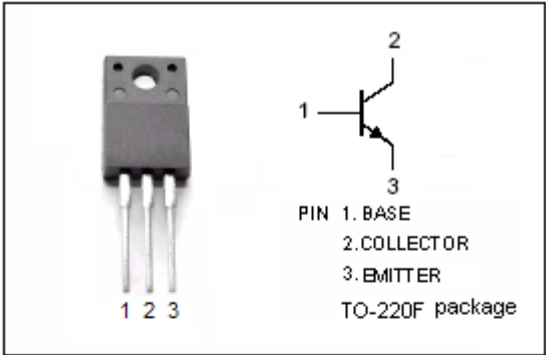
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 35V(\text{Min})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 0.5V(\text{Max}) @ (I_C = 5A, I_B = 0.3A)$
- Complement to Type 2SA1643

APPLICATIONS

- Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	35	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	7	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	25	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



ISC Silicon NPN Power Transistor**2SC4327****ELECTRICAL CHARACTERISTICS****T_j=25℃ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	35			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.3A			0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 0.3A			1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 50V; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V; I _C = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 5A; V _{CE} = 2V	50			
f _T	Current-Gain—Bandwidth Product	I _E = -1A; V _{CE} = 12V		115		MHz